



ME2139

ULTRA-SMALL PACKAGE PWM/PFM SWITCHING CONTROL

STEP-UP SWITCHING REGULATOR

General Description

The ME2139 series is a CMOS step-up switching regulator which mainly consists of a reference voltage source, an oscillation circuit, an error amplifier, a phase compensation circuit, a PWM/PFM switching control circuit. With an external low-ON-resistance Nch Power MOS, this product is applicable to applications requiring high efficiency and high output current. The ME2139 series switches its operation to the PFM control circuit whose duty ratio is 15 % with to the PWM/PFM switching control circuit under a light load and to prevent decline in the efficiency by IC operation current.

Features

- Low voltage operation: Start-up is guaranteed from 0.9 V(IOUT =1 mA)
- Duty ratio: Built-in PWM/PFM switching control circuit 15 to 78 %.
- oscillator frequency: 1.0MHz
- External parts: coil, diode, capacitor, and transistor
- Output voltage range: <20V
- Feedback voltage accuracy: ±2%
- Soft start function: 2 ms

Applications

- MP3 players, digital audio players
- Digital cameras, GPS, wireless transceiver
- Portable devices

Package

• 5-pin SOT23-5



Typical Application Circuit







Selection Guide



product series	switching transistor	CE function	VDD function	FB function	features
ME2139FM5G	External Transistor	Yes	Yes	Yes	Ext +Feedback

Pin Configuration



SOT-23-5

Pin Assignment

ME2139FM5G

Pin Number SOT-23-5	Pin Name	Function
001 200		
1	FB	Feed Back voltage pin
2	VDD	IC power supply pin
3	CE	Shutdown pin
4	GND	GND pin
5	EXT	External transistor connection pin



Block Diagram



Absolute Maximum Rangs

PARAMETER	SYMBOL	RATINGS	UNITS
VDD Pin Voltage	VDD	-0.3~6.5	V
EXT Pin Voltage	EXT	-0.3~VDD+0.3	V
CE Pin Voltage	VCE	-0.3~VDD+0.3	V
EXT Pin Voltage	IEXT	±1000	mA
Power Dissipation (SOT23-5)	Pd	300	mW
Operating Temperature Range	T _{Opr}	-25~+85	°C
Storage Temperature Range	T _{stg}	-40~+125	°C



Electrical Characteristics

ME2139FxxG

Measuring conditions: VDD=VCE=3.3V, Topt=25°C. Unless otherwise specified.

Parameter	SYMBOL	CONDITION		MIN	TYP	MAX	UNIT	Circuit
Feedback voltage	V_{FB}	-		1.225	1.25	1.275	V	2
Input voltage	V _{IN}	-			-	6	V	2
Operation start voltage	V _{ST}	I _{OUT} =1mA		-	-	0.9	V	2
Operation holding voltage	V _{HLD}	I _{OUT} =1mA , Measured voltage gradually	by decreasing VIN	0.7	-	-	V	2
Current consumption 1	I _{SS1}	V _{FB} =V _{FB} (S)× 0.95		-	200	-	μA	1
Current consumption 2	I _{SS2}	V _{FB} =1.5V		-	15	-	μA	1
Current consumption during shutdown	I _{SSS}	V _{CE} =0V		-	0.02	0.5	μA	1
EXT pin output	I _{EXTH}	V _{EXT} =V _{OUT} -0.4V		-	-25	-	mA	1
current	I _{EXTL}	V _{EXT} =0.4V			40	-	mA	1
Feed back voltagetemperature coefficient		Ta=-25-85℃		-	±50	-	ppm/°C	2
Oscillation frequency	Fosc	-		0.8	1.0	1.2	MHz	1
Max. duty ratio	MAXDUTY	V _{FB} =V _{FB} (S)× 0.95		-	78	-	%	1
PWM/PFM switchingduty ratio	PFMDUTY	V _{FB} =V _{FB} (S)× 1.5, no load		-	15	-	%	1
Shutdown pin input voltage	V_{SH}	Measured the oscillation at EXT pin		0.75	-	-	V	1
	V _{SL1}	Judged the stop of oscillation at EXT pin	V _{OUT} ≥1.5V	-	-	0.3	V	1
	V _{SL2}		V _{OUT} <1.5V	-	-	0.2	V	1
Shutdown pin input	I _{SH}	V _{CE} =V _{FB} (S)×0.95		-0.1	-	0.1	μA	1
voltage	I _{SL}	V _{CE} =0V		-0.1	-	0.1	μA	1
Soft start time	tss	-		-	2	-	mS	2
Efficiency	EFFI	-		-	90	-	%	2

1. VOUT(S) is the set output voltage value, and VOUT is the typital value of the output voltage.

2. VOUT(S) can be set by using the rate of VFB and output voltage setting resisitors(R1,R2).

3. VFB(S) is the set output voltage value.

4. This product from the start when the VDD=0.9V booster work , but in order to stabilize the output voltage and oscillation frequency ,to control the VDD, 2.5V ≦ VDD<6V.



Test Circuit:



2.



External parts (suggest)

- 1. Diode use Schottky diode such as SS14 or SS34 forward voltage drop:0.2V)
- 2、NMOS: MEM8205 or MEM2310
- 3. Inductor: 3.3 μ H (r<0.5 Ω)
- $4\,{\scriptstyle \smallsetminus}\,$ Capacitor: Tantalum type 22uF



External parts selection for DC/DC converter

The relationship between major characteristics of the step-up circuit and characteristics parameters of the external





Figure 1 Relationship between major characteristics of the step-up circuit and external parts

1. Inductor

An inductance has strong influence on maximum output current I_{OUT} and efficiency η .1.

Figure 2 shows the relation between I_{OUT} , and η characteristics to L of ME2139F.





The peak current (I_{PK}) increases by decreasing L and the stability of a circuit improves and I_{OUT} increases. If L is



furthermore made small, efficiency falls and in running short, I_{OUT} decreases. (Based on the current drive capability of external switching transistor.)

The loss of I_{PK} by the switching transistor decreases by increasing L and the efficiency becomes maximum at a certain L value. Further increasing L decreases efficiency due to the loss of DC resistance of the coil. Also, I_{OUT} decreases, too.

Oscillation frequency is higher, smaller one can be chose and also makes coil smaller. The recommended inductances are 2.2 to 4.7 μ H inductor for ME2139F.

Choose a value for L by referring to the reference data because the maximum output current is due to the input voltage in an actual case. Choose an inductor so that I_{PK} does not exceed the allowable current. Exceeding the allowable current of the inductor causes magnetic saturation, remarkable low efficiency and destruction of the IC chip due to a large current.

IPK in uncontinuous mode is calculated from the following equation:

$$I_{PK} = \sqrt{\frac{2I_{OUT}(V_{OUT} + V_D - V_{IN})}{f_{OSC}.L}} (A)$$

Fosc = oscillation frequency, VDD =0.4 V.

2. Diode

Use an external diode that meets the following requirements:

• Low forward voltage: (VF<0.3 V)

• High switching speed: (50 ns max.)

- Reverse voltage: VOUT + VF or more
- Rated current: IPK or more

3. Capacitor (CIN, Co)

To improve efficiency, an input capacitor (C_{IN}) lowers the power supply impedance and averages the input current. Select C_{IN} according to the impedance of the power supply used. The recommended capacitance is 10µF for the ME2139F.

An output capacitor (C_{OUT}), which is used to smooth the output voltage, requires a capacitance larger than that of the step-down type because the current is intermittently supplied from the input to the output side in the step-up type. A 22µF ceramic capacitor is recommended for the ME2139F. However, a higher capacitance is recommended if the output voltage is high or the load current is large. If the output voltage or load current is low,

about 10µF can be used without problems.

Select C_{OUT} after sufficient evaluation with actual application.

A ceramic capacitor can be used for both the input and output.



4. Enhancement MOS FET type

Depending on the MOS FET you use in your device, there is a chance of a current overrun at power ON. Thoroughly test all settings with your device before deciding on which one to use. Also, try to use a MOS FET with the input capacitance of 700 pF or less.

Since the ON resistor of the MOS FET might depend on the difference between the output voltage VouT and the threshold voltage of MOS FET, and affect the output current as well as the efficiency, the threshold voltage should be low. When the output voltage is low, the circuit operates only when the MOS FET has the threshold voltage lower than the output voltage.

5. Precautions

- Mount external capacitors, a diode, and a coil as close as possible to the IC.
- Unique ripple voltage and spike noise occur in switching regulators. Because they largely depend on the coil and the capacitor used, check them using an actually mounted model.
- •Make sure dissipation of the switching transistor (especially at a high temperature) does not exceed the allowable power dissipation of the package.

• The performance of this IC varies depending on the design of the PCB patterns, peripheral circuits and external parts. Thoroughly test all settings with your device. Also, try to use recommended external parts.



Typical Performance Characteristics







Packaging Information



ЫМ	Millim	eters	Inches		
	Min	Max	Min	Max	
A	0.9	1.45	0.0354	0.0571	
A1	0	0.15	0	0.0059	
A2	0.9	1.3	0.0354	0.0512	
A3	0.6	0.7	0.0236	0.0276	
b	0.25	0.5	0.0098	0.0197	
С	0.1	0.26	0.0039	0.0102	
D	2.8	3.1	0.1102	0.122	
e1	1.9(TYP)		0.0748(TYP)		
E	2.6	3.1	0.1024	0.1201	
E1	1.5	1.8	0.05118113	0.07086618	
е	0.95(TYP)	0.0374(TYP)		
L	0.25	0.6	0.0098	0.0236	
L1	0.59(TYP)		0.0232(TYP)		
θ	0	8°	0	8°	
c1	0.2(TYP)		0.0079(TYP)		



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